



## Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=3mA, T_{vj}=25$	5.0	6.2	7.0	V
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50A, V_{GE}=15V, T_{vj}=25$		1.85		V
		$I_C=50A, V_{GE}=15V, T_{vj}=125$		2.05		
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25$		4.29		nF

Reverse Transfer Capacitance

$C_{Tm0} g0 G(C)JTJETOEM/P/AMCID 183/Lang(en-US)BDCqBT/F9 6.96 Tf/GS7 gs0.750 w1 j1 0 0.489990 551.590027 Tm0 g0 G(Tm0 g0 G(C)JT$

## ● Diode

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25$	1200	V
Continuous DC Forward Current	$I_F$		50	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1\text{ms}$	100	A

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	$V_F$	$I_F=50\text{A}, T_{vj}=25$		1.95	2.20	V
		$I_F=50\text{A}, T_{vj}=125$		2.05		
Recovered Charge	$Q_{rr}$	$I_F=50\text{A}$		2.77		uC

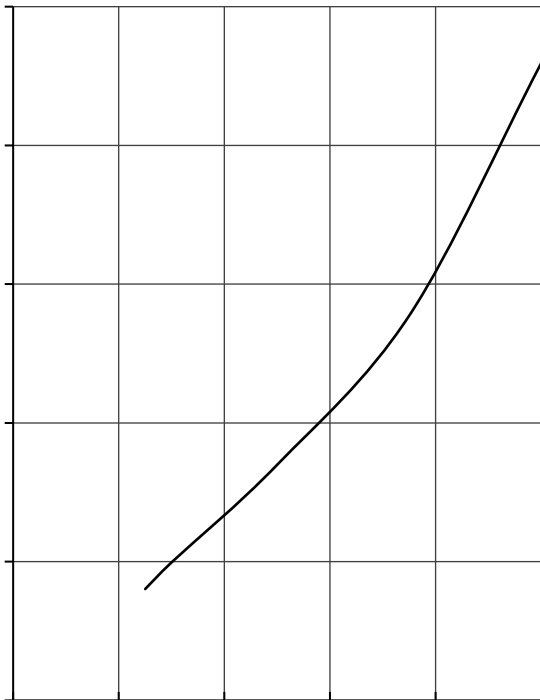
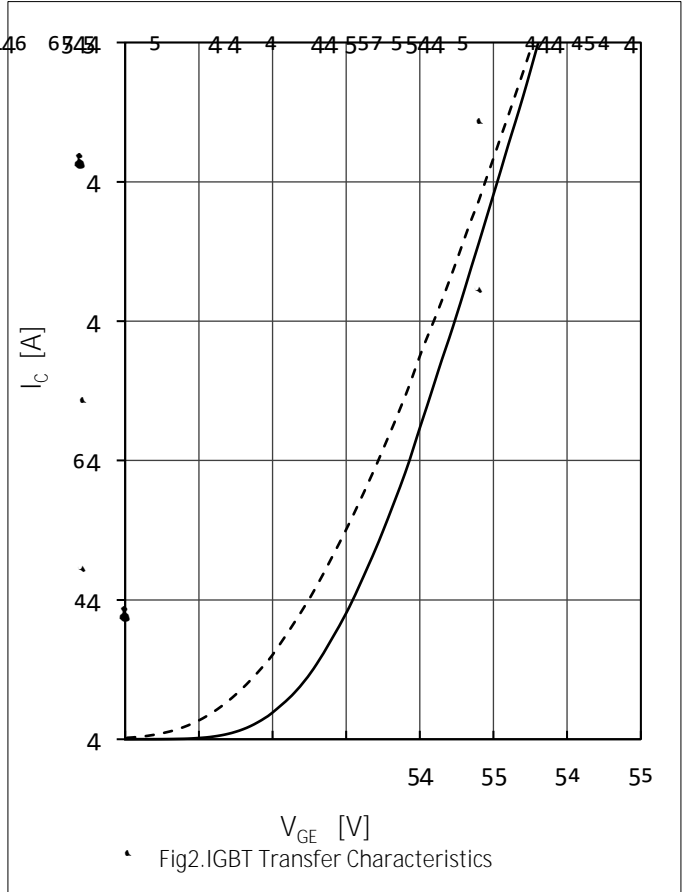
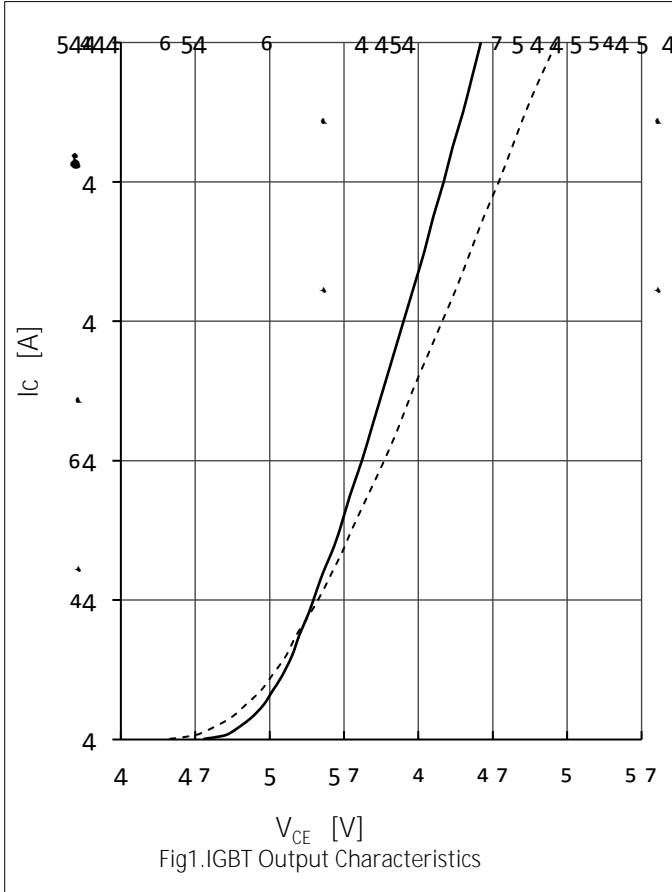
Peak Reverse Recovery/GS7 gs0.750 w1 j1 0 0 1 4 G1 j1 0 0 BDCqBT/F9 10.56 Tf/GS7 gs0.750 w1 j1 0 0 1 451.299988 461648999098T  
 $V_R=600\text{V}$   
 $-di_F/dt=800\text{A/us}$   
 $T_{vj}=25$

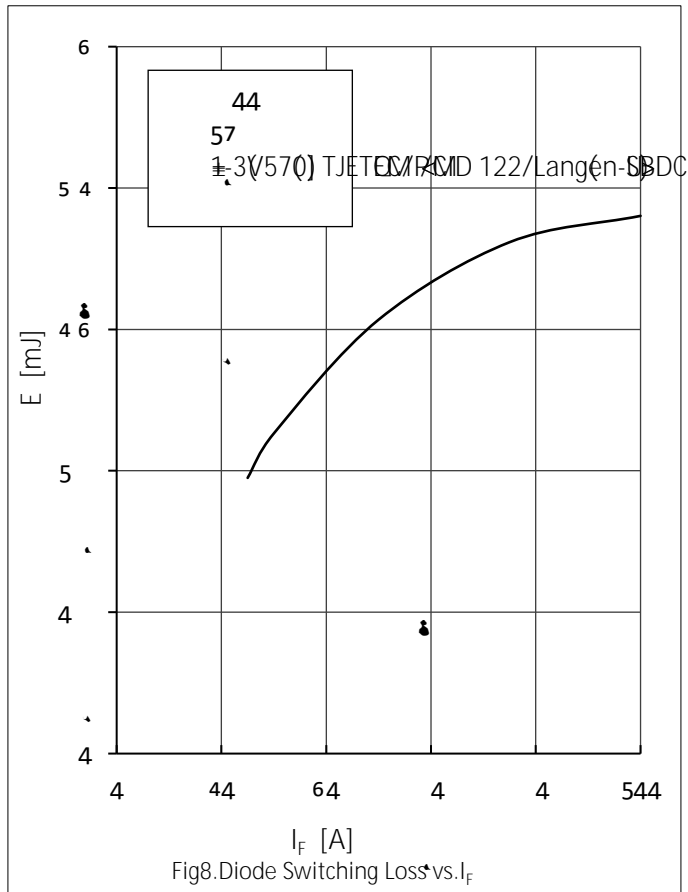
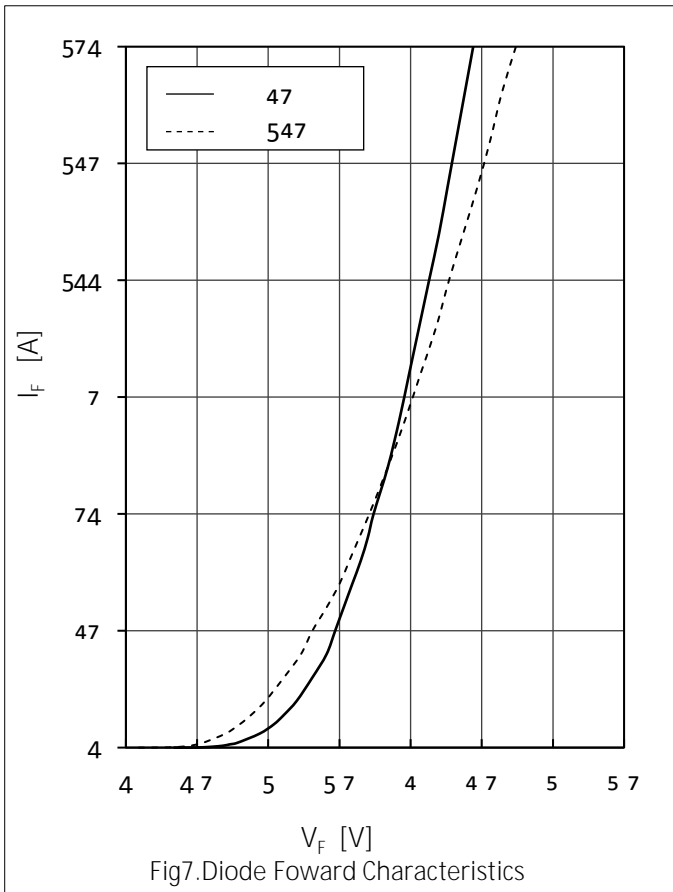
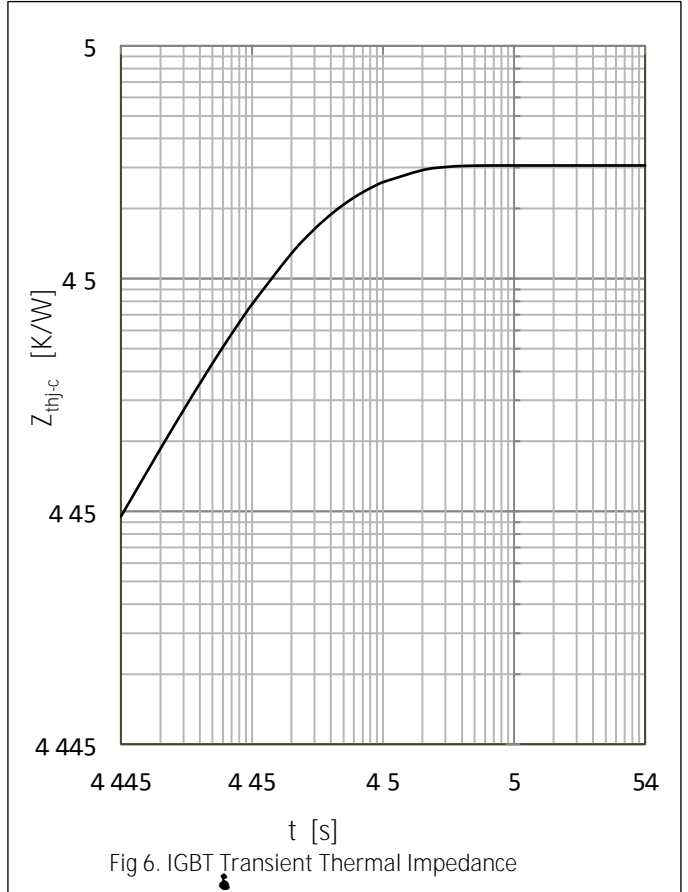
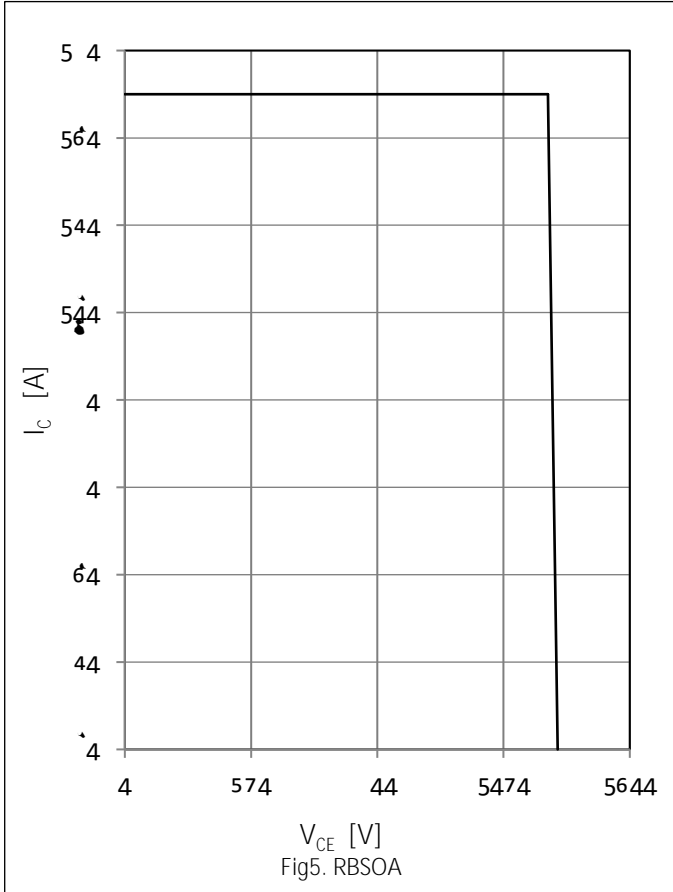


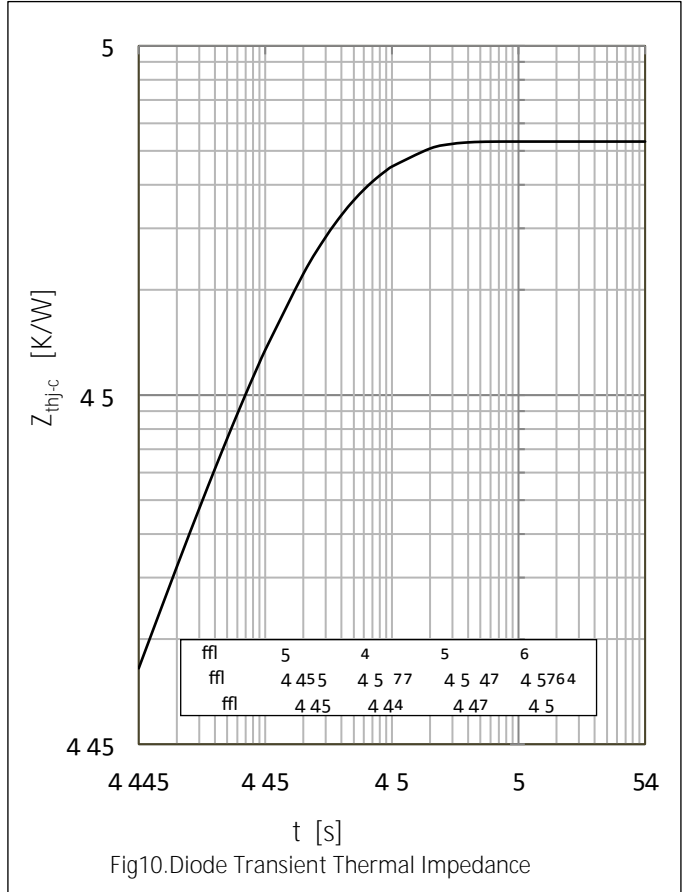
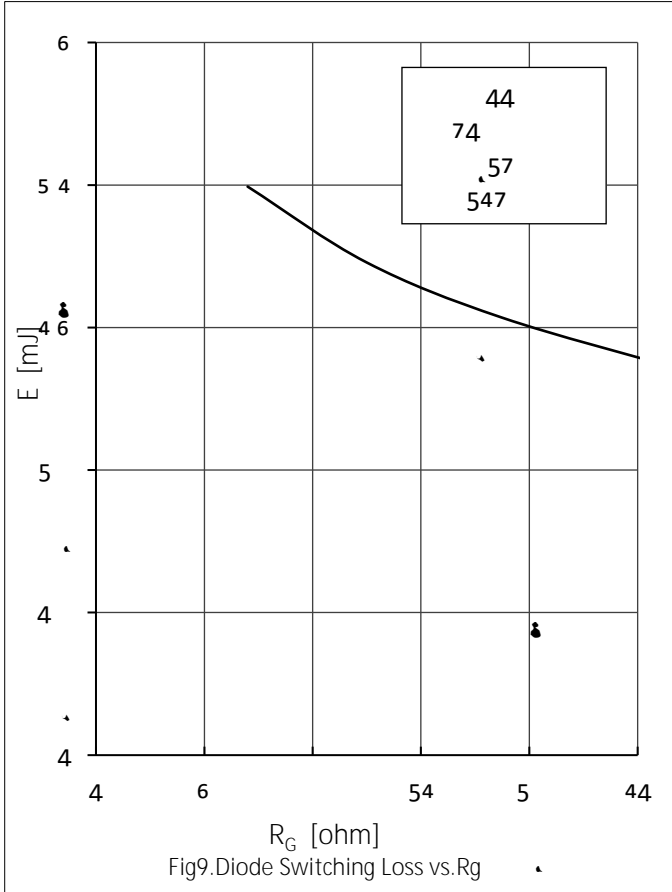
## ● Module Characteristics

T<sub>C</sub>=25°C unless otherwise specified

Parameter	Symbol
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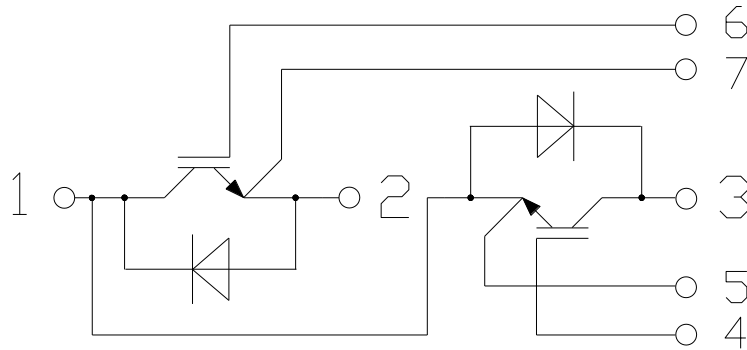








## ● Circuit Diagram



## ● Package Outline Information

Dimensions in Millimeters

